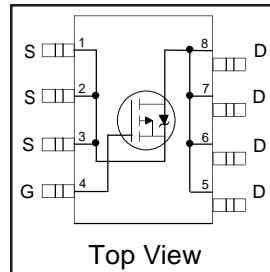


Si4435DYPbF

HEXFET® Power MOSFET

- Ultra Low On-Resistance
- P-Channel MOSFET
- Surface Mount
- Available in Tape & Reel
- Lead-Free

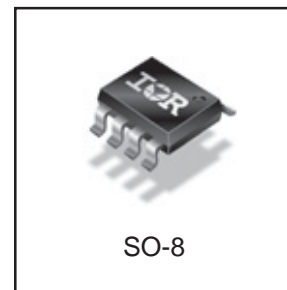


$V_{DSS} = -30V$
$R_{DS(on)} = 0.020\Omega$

Description

These P-channel HEXFET® Power MOSFETs from International Rectifier utilize advanced processing techniques to achieve the extremely low on-resistance per silicon area. This benefit provides the designer with an extremely efficient device for use in battery and load management applications..

The SO-8 has been modified through a customized leadframe for enhanced thermal characteristics and multiple-die capability making it ideal in a variety of power applications. With these improvements, multiple devices can be used in an application with dramatically reduced board space. The package is designed for vapor phase, infrared, or wave soldering techniques.



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain- Source Voltage	-30	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V$	-8.0	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ -10V$	-6.4	
I_{DM}	Pulsed Drain Current ①	-50	
$P_D @ T_A = 25^\circ C$	Power Dissipation	2.5	W
$P_D @ T_A = 70^\circ C$	Power Dissipation	1.6	
	Linear Derating Factor	0.02	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150	°C

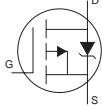
Thermal Resistance

	Parameter	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient③	50	°C/W

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

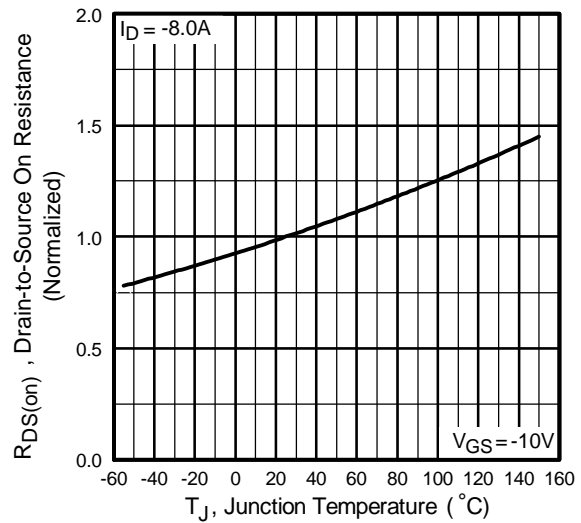
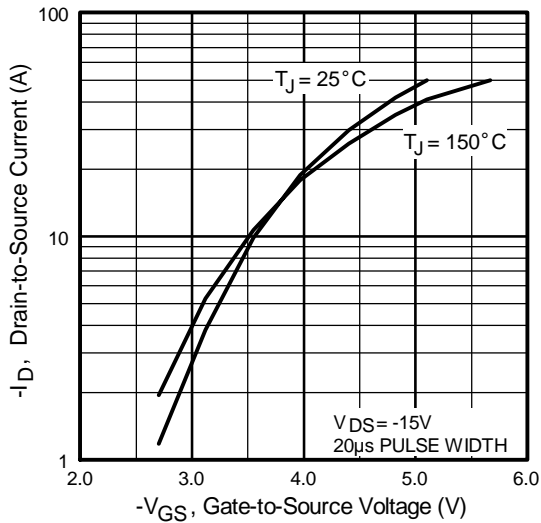
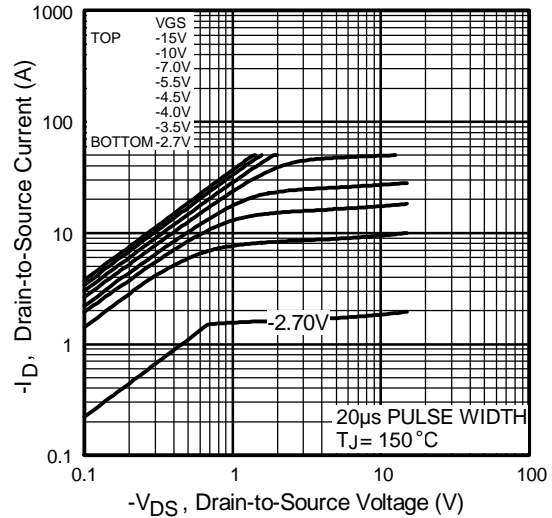
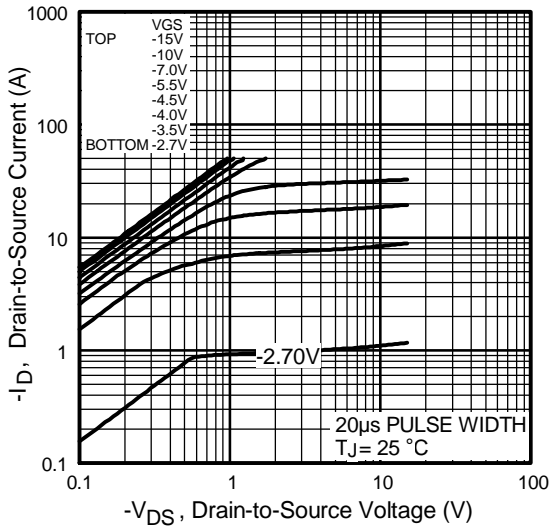
	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	-30	—	—	V	V _{GS} = 0V, I _D = -250μA
ΔV _{(BR)DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	-0.019	—	V/°C	Reference to 25°C, I _D = -1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	0.015	0.020	Ω	V _{GS} = -10V, I _D = -8.0A ②
		—	0.026	0.035		V _{GS} = -4.5V, I _D = -5.0A ②
V _{GS(th)}	Gate Threshold Voltage	-1.0	—	—	V	V _{DS} = V _{GS} , I _D = -250μA
g _{fs}	Forward Transconductance	—	11	—	S	V _{DS} = -15V, I _D = -8.0A
I _{DSS}	Drain-to-Source Leakage Current	—	—	-10	μA	V _{DS} = -24V, V _{GS} = 0V
		—	—	-10		V _{DS} = -15V, V _{GS} = 0V, T _J = 70°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	-100	nA	V _{GS} = -20V
	Gate-to-Source Reverse Leakage	—	—	100		V _{GS} = 20V
Q _g	Total Gate Charge	—	40	60	nC	I _D = -4.6A
Q _{gs}	Gate-to-Source Charge	—	7.1	—		V _{DS} = -15V
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	8.0	—		V _{GS} = -10V ②
t _{d(on)}	Turn-On Delay Time	—	16	24	ns	V _{DD} = -15V, V _{GS} = -10V ②
t _r	Rise Time	—	76	110		I _D = -1.0A
t _{d(off)}	Turn-Off Delay Time	—	130	200		R _G = 6.0Ω
t _f	Fall Time	—	90	140		R _D = 15Ω
C _{iss}	Input Capacitance	—	2320	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	390	—		V _{DS} = -15V
C _{rss}	Reverse Transfer Capacitance	—	270	—		f = 1.0kHz

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	-2.5	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	-50		
V _{SD}	Diode Forward Voltage	—	—	-1.2	V	T _J = 25°C, I _S = -2.5A, V _{GS} = 0V ②
t _{rr}	Reverse Recovery Time	—	34	51	ns	T _J = 25°C, I _F = -2.5A
Q _{rr}	Reverse Recovery Charge	—	33	50	nC	di/dt = -100A/μs ②

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Pulse width ≤ 300μs; duty cycle ≤ 2%.
- ③ Surface mounted on FR-4 board, t ≤ 5sec.



Si4435DYPbF

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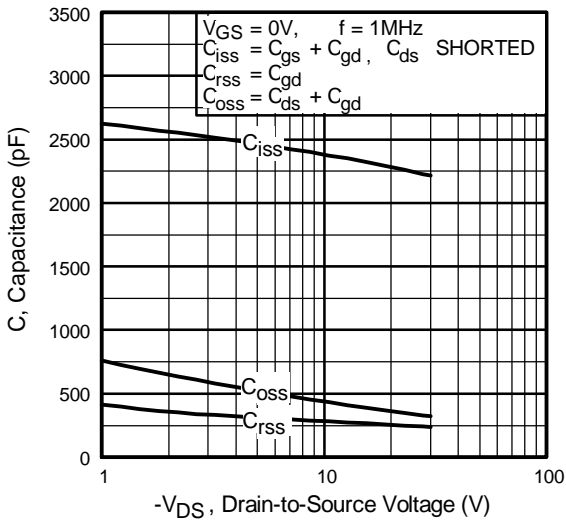


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

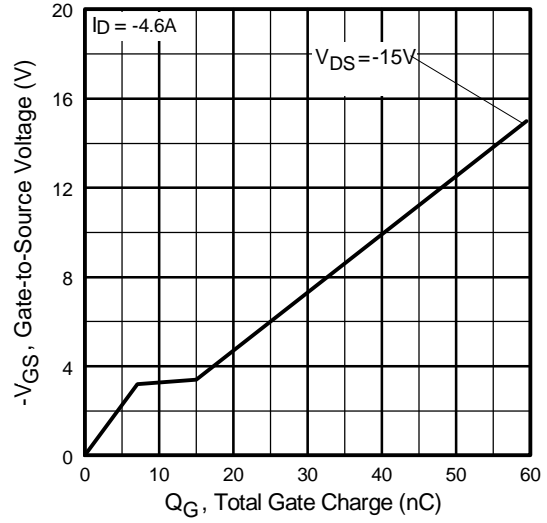


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

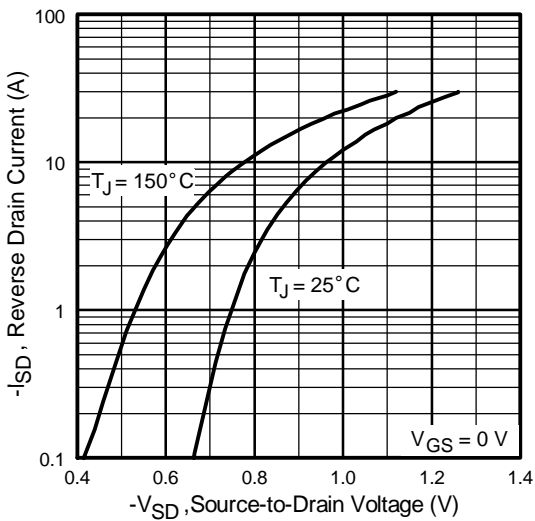


Fig 7. Typical Source-Drain Diode Forward Voltage

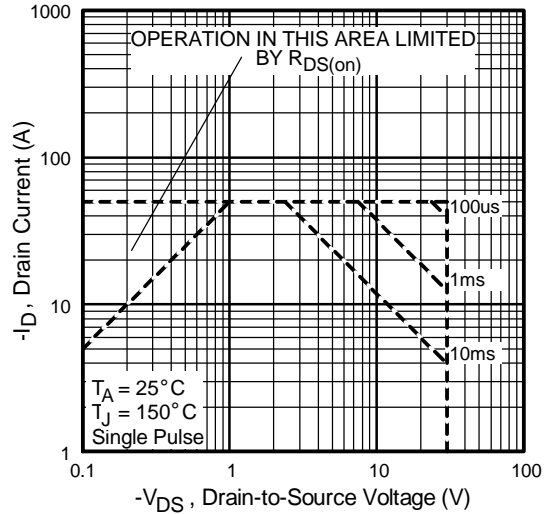


Fig 8. Maximum Safe Operating Area

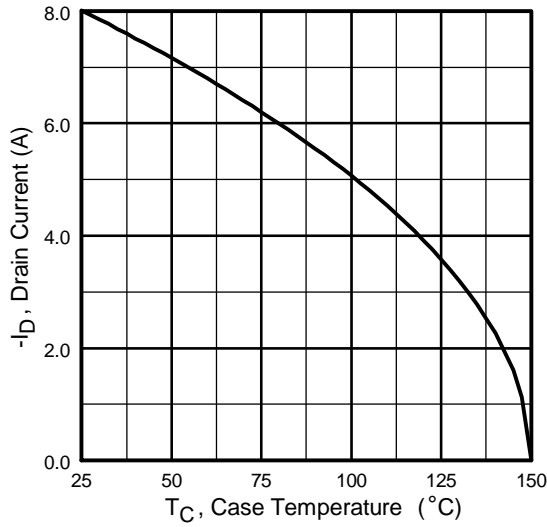


Fig 9. Maximum Drain Current Vs. Case Temperature

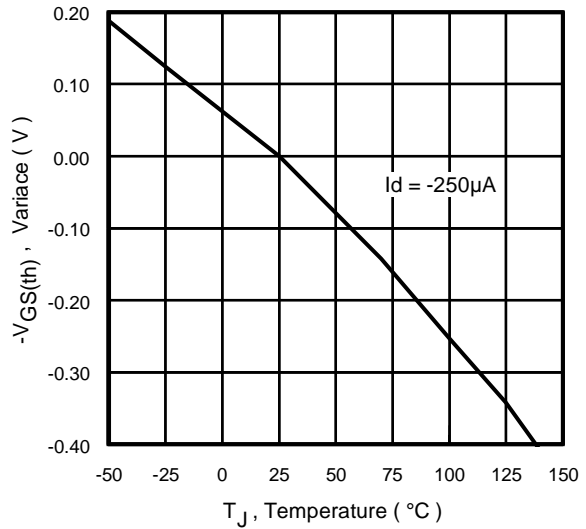


Fig 10. Typical V_{GS(th)} Variance Vs. Junction Temperature

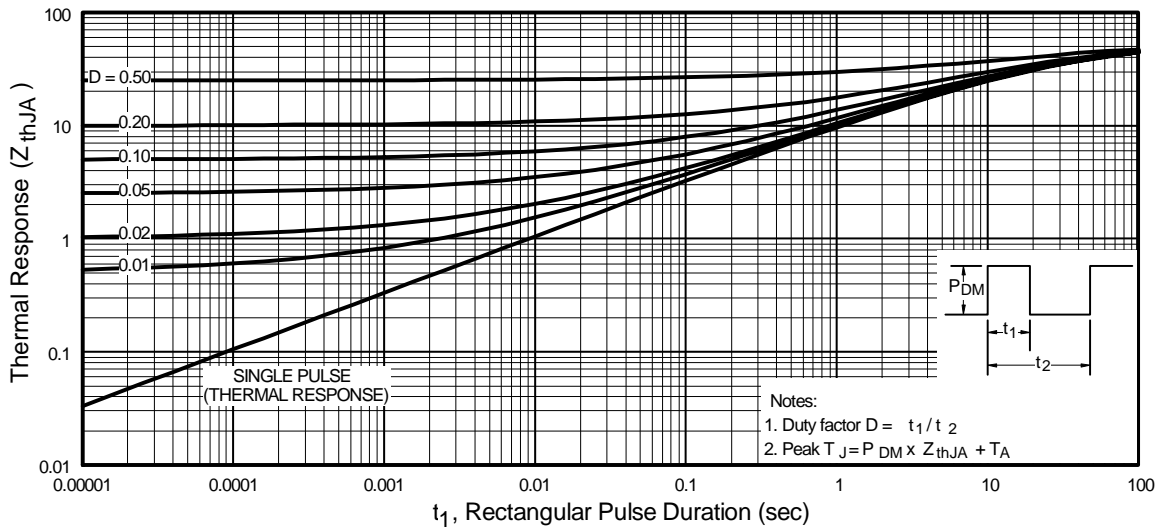


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

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IR Rectifier

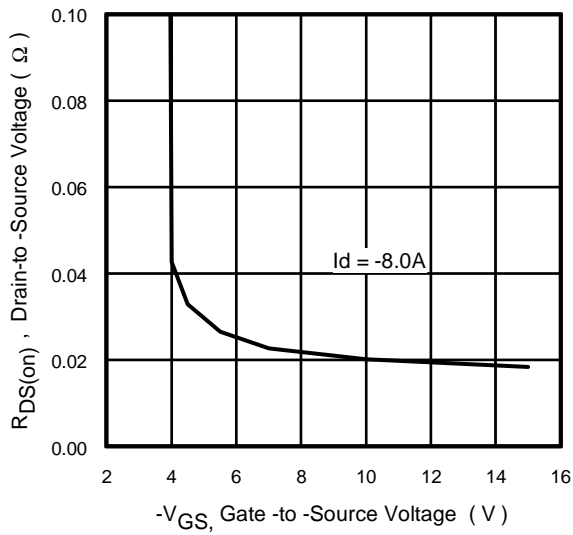


Fig 12. Typical On-Resistance Vs. Gate Voltage

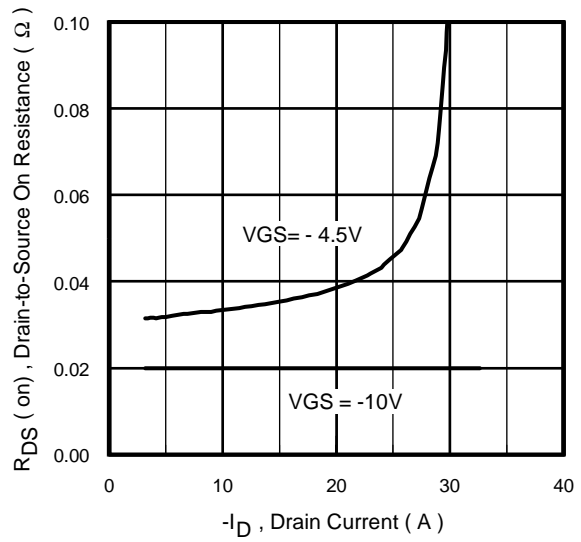
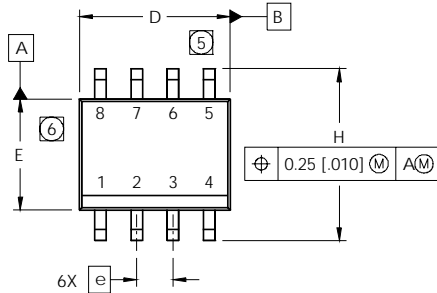


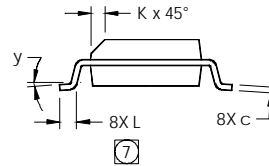
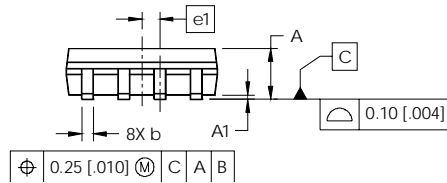
Fig 13. Typical On-Resistance Vs. Drain Current

SO-8 Package Outline

Dimensions are shown in millimeters (inches)

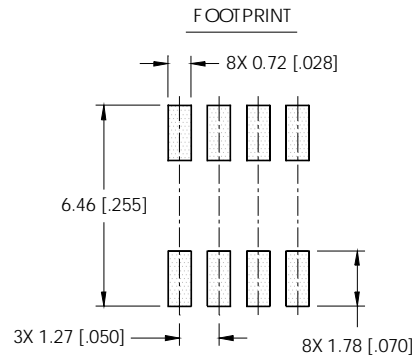


DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°



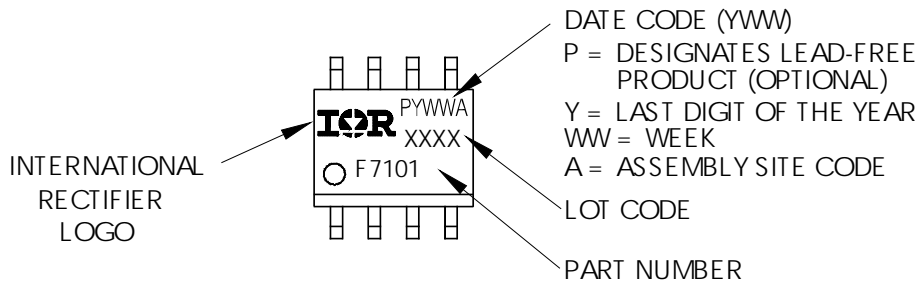
NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
- 5 DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [0.006].
- 6 DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [0.010].
- 7 DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.



SO-8 Part Marking

EXAMPLE: THIS IS AN IRF 7101 (MOSFET)

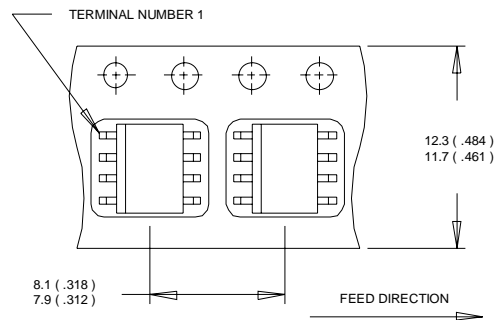


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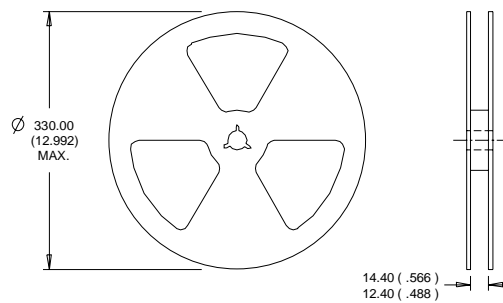
International
IR Rectifier

SO-8 Tape and Reel

Dimensions are shown in millimeters (inches)



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Data and specifications subject to change without notice.
This product has been designed and qualified for the Consumer market.
Qualifications Standards can be found on IR's Web site.

International
IR Rectifier

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TAC Fax: (310) 252-7903

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